

3 A LOW Vf Schottky Barrier Rectifier

DESCRIPTION

This UPS340e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

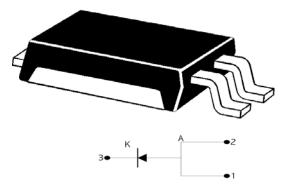
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Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	V
RMS Reverse Voltage	V _{R (RMS)}	28	V
Average Rectified Output Current	Io	3	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T _c =90 °C	I _{FSM}	50	А
Storage Temperature	T _{STG}	-55 to +150	°C
Junction Temperature	T_J	-55 to +125	°C

THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-case (bottom)	R _{eJC}	3.2	°C/ Watt
Junction to ambient (1)	Reja	65	°C/ Watt

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

Powermite 3™



KEY FEATURES

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm
- Options for screening in accordance with MIL-PRF-19500 for JAN, JANTX, and JANTXV are available by adding MQ, MX, or MV prefixes respectively to part numbers. For example, designate MXUPS340e3 for a JANTX (consult factory for Tin-Lead plating).
- Optional 100% avionics screening available by adding MA prefix for 100% temperature cycle, thermal impedance and 24 hours HTRB (consult factory for Tin-Lead plating)

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I_{RM}
- Small foot print 190 X 270 mils (1:1 Actual size)
 See mounting pad details on pg 3

MECHANICAL & PACKAGING

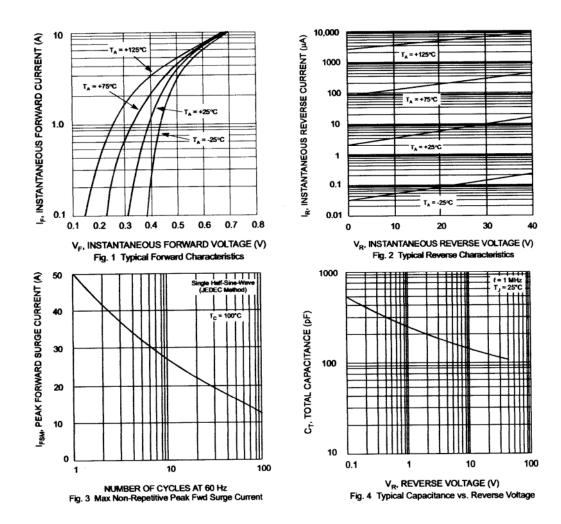
- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S340•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel



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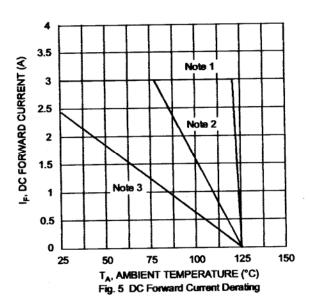
ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)	V _F	$I_F = 3 \text{ A}$, $T_j = 25 \text{ °C}$ $I_F = 3 \text{ A}$, $T_j = 125 \text{ °C}$ $I_F = 6 \text{ A}$, $T_j = 25 \text{ °C}$ $I_F = 6 \text{ A}$, $T_j = 125 \text{ °C}$		0.46 0.40 0.57 0.54	0.50 0.44 0.61 0.58	V
Reverse Break Down Voltage (Note 1)	V_{BR}	I _R = 0.5 mA	40			٧
Reverse Current (Note1)	I _R	$V_R = 40V, T_j = 25 ^{\circ}\text{C}$ $V_R = 40V, T_j = 100 ^{\circ}\text{C}$		15 10	500 20	uA mA
Capacitance	Ст	$V_R = 4 \text{ V; } f = 1 \text{ MH}_Z$		180		pF

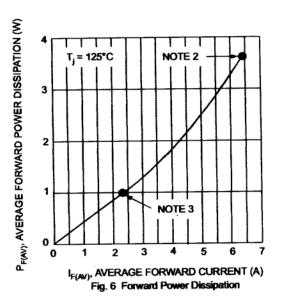
Note: 1 Short duration test pulse used to minimize self – heating effect.





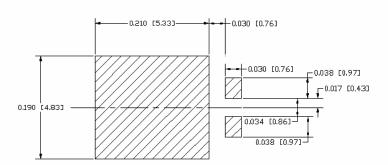
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- Notes: 1. $T_A = T_{SOLDERING\ POINT}$, $R_{\Theta JS} = 3.2^{\circ}\ C/W$ $R_{\Theta SA} = 0^{\circ}\ C/W$.
 - Device mounted on GETEK substrate, 2" x 2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". R_{⊙JA} in range of 20-40° C/W.
 - 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout $R_{\Theta JA}$ in range of 65° C/W. See mounting pad below.

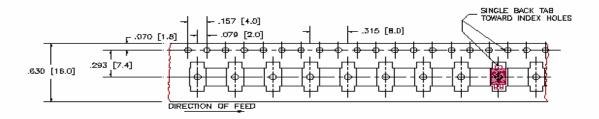
MOUNTING PAD DIMENSIONS (inches)



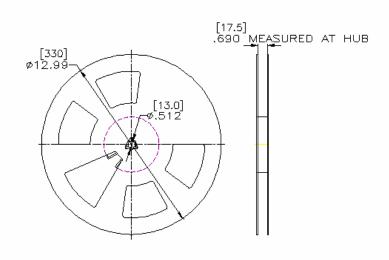


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TAPE & REEL



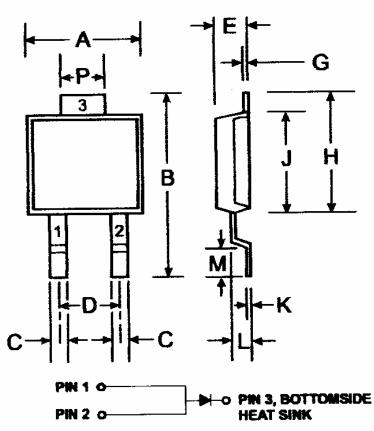
13 INCH REEL





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PACKAGE DIMENSIONS



Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

POWERMITE®3			
Dim	Min	Max	
A	4.03	4.09	
В	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
M	.36	.46	
P	1.73	1.83	
All Dimensions in mm			



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